

## N-Channel Power MOSFET

800V, 12A, 400mΩ

### FEATURES

- Super-Junction technology
- High performance, small  $R_{DS(ON)} * Q_g$  figure of merit (FOM)
- High ruggedness performance
- 100% UIS and  $R_g$  tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
$V_{DS}$	800	V
$R_{DS(on)}$ (max)	400	mΩ
$Q_g$	51	nC

### APPLICATIONS

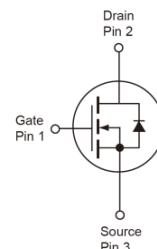
- Power Supply
- AC/DC LED Lighting



ROHS  
COMPLIANT

HALOGEN  
FREE

ITO-220S



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	800	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current <sup>(Note 1)</sup>	$I_D$	12	A
		7.5	A
Pulsed Drain Current <sup>(Note 2)</sup>	$I_{DM}$	48	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_D$	69	W
Single Pulse Avalanche Energy <sup>(Note 3)</sup>	$E_{AS}$	812	mJ
Single Pulse Avalanche Current <sup>(Note 3)</sup>	$I_{AS}$	5.7	A
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to +150	°C

### THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	1.8	°C/W
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	62	°C/W

**Thermal Performance Note:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted)						
<b>PARAMETER</b>	<b>CONDITIONS</b>	<b>SYMBOL</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNIT</b>
<b>Static</b> <sup>(Note 4)</sup>						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$ , $I_D = 250\mu\text{A}$	$BV_{DSS}$	800	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	$V_{GS(\text{TH})}$	2	3.3	4	V
Gate Body Leakage	$V_{GS} = \pm 30\text{V}$ , $V_{DS} = 0\text{V}$	$I_{GSS}$	--	--	$\pm 100$	nA
Zero Gate Voltage Drain Current	$V_{DS} = 800\text{V}$ , $V_{GS} = 0\text{V}$	$I_{DSS}$	--	--	1	$\mu\text{A}$
Drain-Source On-State Resistance	$V_{GS} = 10\text{V}$ , $I_D = 2.7\text{A}$	$R_{DS(\text{on})}$	--	300	400	$\text{m}\Omega$
<b>Dynamic</b> <sup>(Note 5)</sup>						
Total Gate Charge	$V_{DS} = 640\text{V}$ , $I_D = 8\text{A}$ , $V_{GS} = 10\text{V}$	$Q_g$	--	51	--	nC
Gate-Source Charge		$Q_{gs}$	--	10	--	
Gate-Drain Charge		$Q_{gd}$	--	24	--	
Input Capacitance	$V_{DS} = 100\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1.0\text{MHz}$	$C_{iss}$	--	1848	--	pF
Output Capacitance		$C_{oss}$	--	90	--	
Gate Resistance	$f = 1.0\text{MHz}$	$R_g$	--	3.3	6.6	$\Omega$
<b>Switching</b> <sup>(Note 6)</sup>						
Turn-On Delay Time	$V_{DD} = 400\text{V}$ , $I_D = 8\text{A}$ , $V_{GS} = 10\text{V}$ , $R_{GEN} = 5\Omega$	$t_{d(on)}$	--	19	--	ns
Turn-On Rise Time		$t_r$	--	26	--	
Turn-Off Delay Time		$t_{d(off)}$	--	57	--	
Turn-Off Fall Time		$t_f$	--	28	--	
<b>Source-Drain Diode</b> <sup>(Note 4)</sup>						
Body-Diode Continuous Forward Current		$I_S$	--	--	8	A
Body-Diode Pulsed Current		$I_{SM}$	--	--	32	A
Forward Voltage	$I_S = 8\text{A}$ , $V_{GS} = 0\text{V}$	$V_{SD}$	--	--	1.4	V
Reverse Recovery Time	$I_S = 8\text{A}$ $dI_F/dt = 100\text{A}/\mu\text{s}$	$t_{rr}$	--	340	--	ns
Reverse Recovery Charge		$Q_{rr}$	--	4.9	--	$\mu\text{C}$

**Notes:**

1. Current limited by package.
2. Pulse width limited by the maximum junction temperature.
3.  $L = 50\text{mH}$ ,  $I_{AS} = 5.7\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse test:  $PW \leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

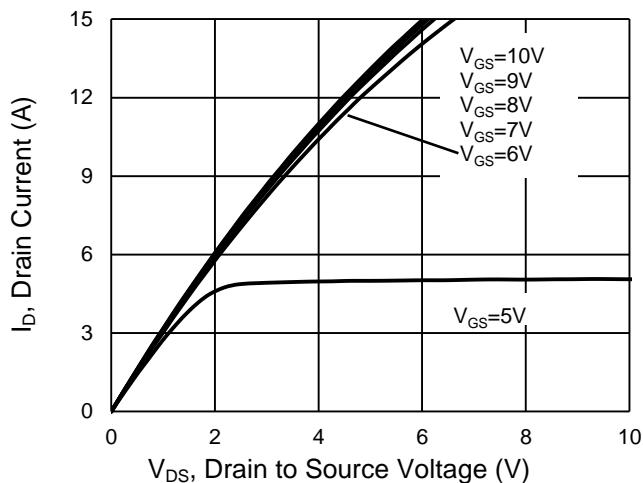
**ORDERING INFORMATION**

<b>PART NO.</b>	<b>PACKAGE</b>	<b>PACKING</b>
TSM80N400CF C0G	ITO-220S	50pcs / Tube

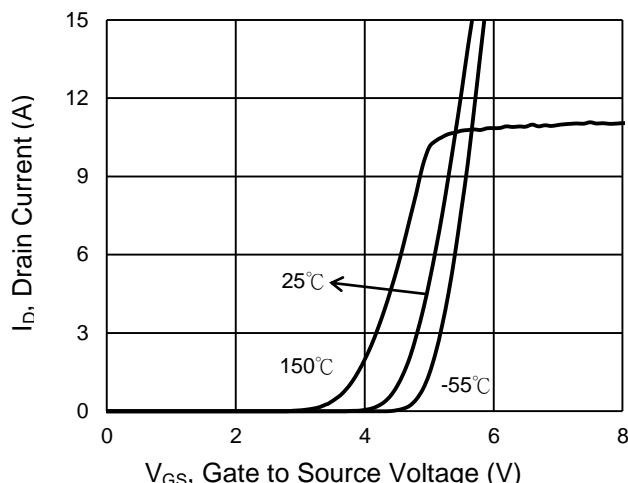
## CHARACTERISTICS CURVES

( $T_C = 25^\circ\text{C}$  unless otherwise noted)

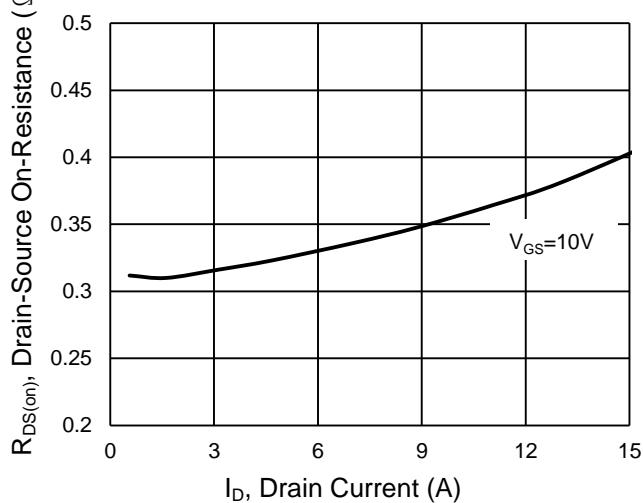
**Output Characteristics**



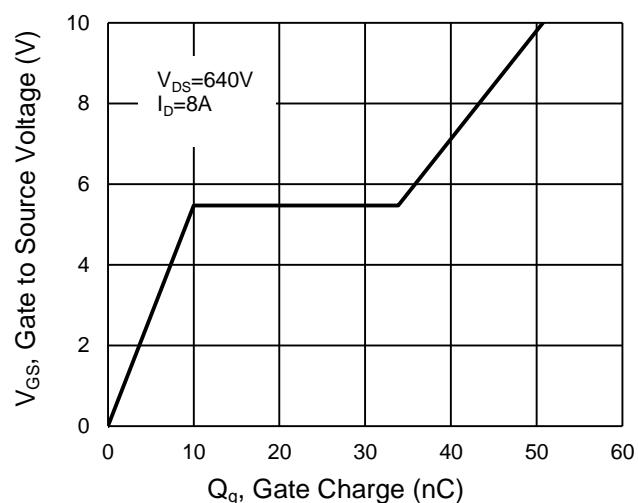
**Transfer Characteristics**



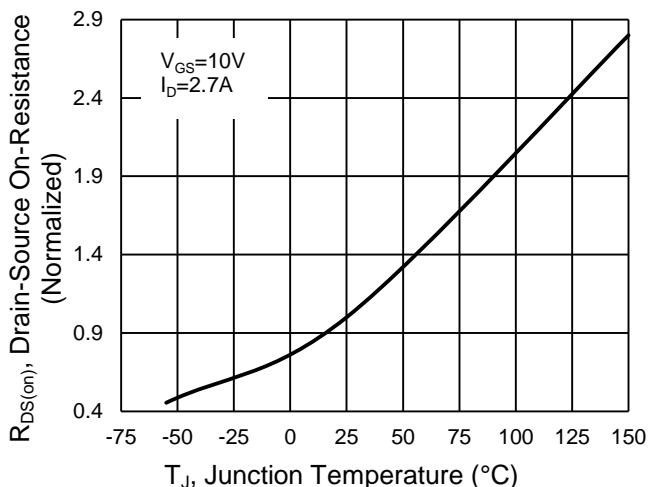
**On-Resistance vs. Drain Current**



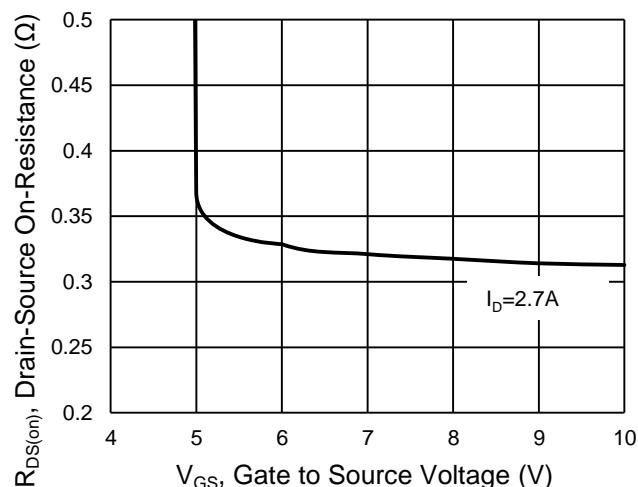
**Gate-Source Voltage vs. Gate Charge**



**On-Resistance vs. Junction Temperature**



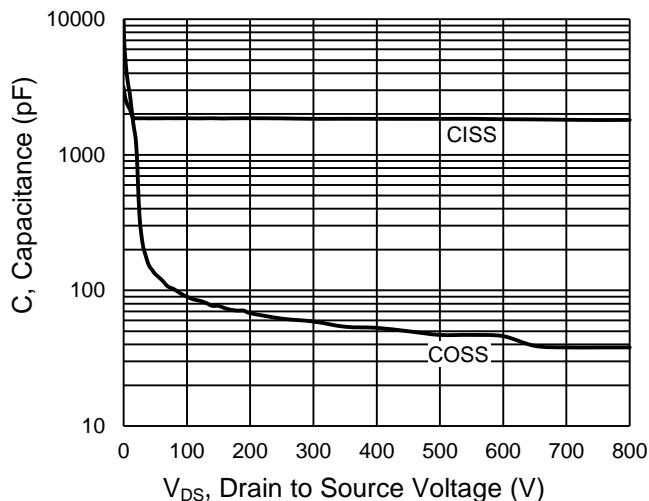
**On-Resistance vs. Gate-Source Voltage**



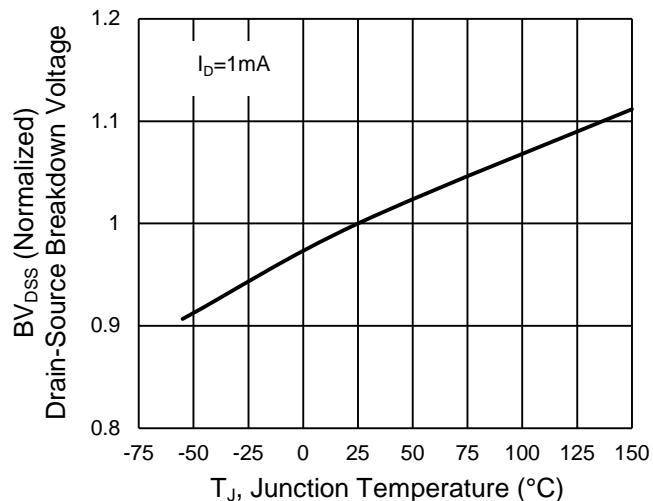
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( $T_C = 25^\circ\text{C}$  unless otherwise noted)

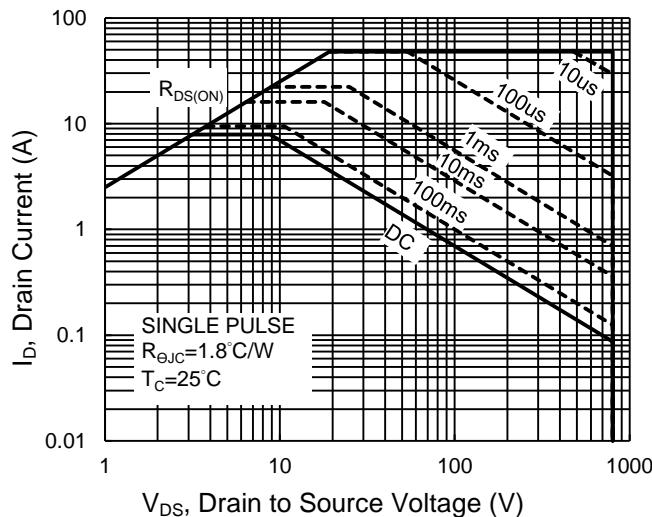
**Capacitance vs. Drain-Source Voltage**



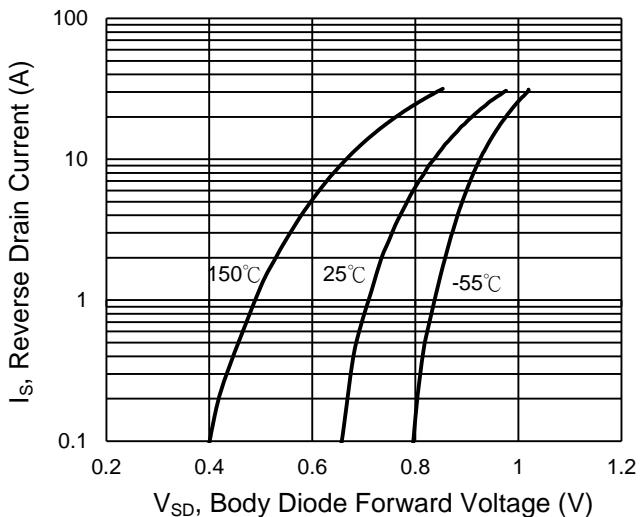
**$\text{BV}_{\text{DSS}}$  vs. Junction Temperature**



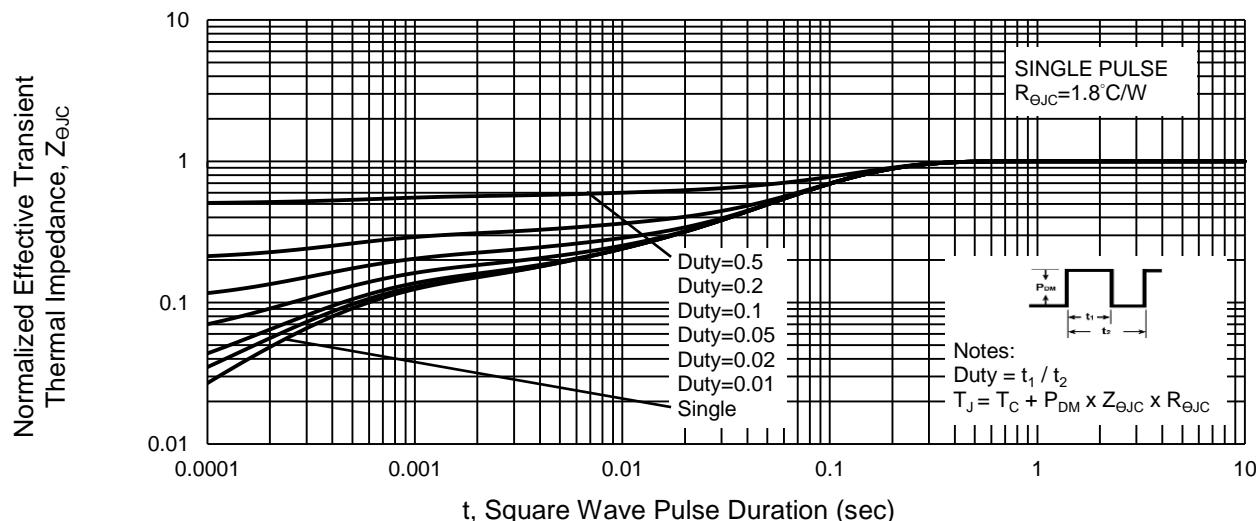
**Maximum Safe Operating Area, Junction-to-Case**



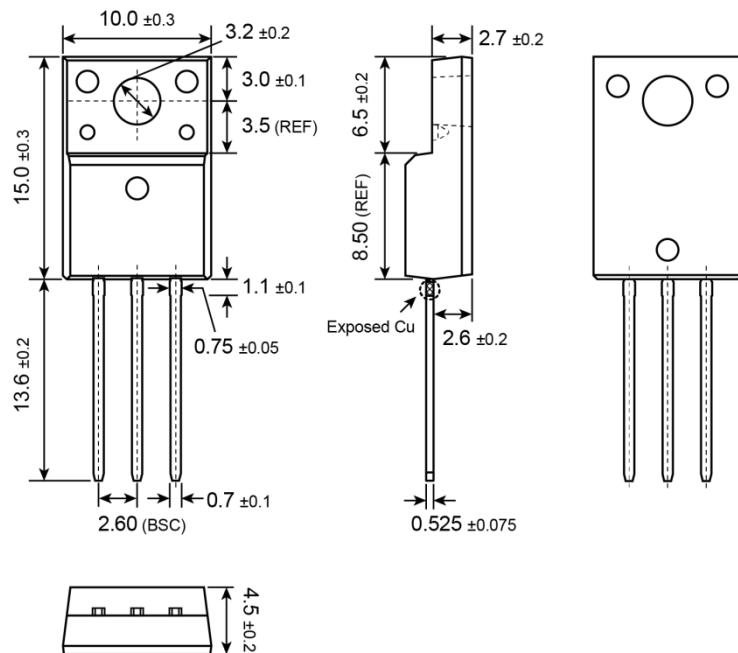
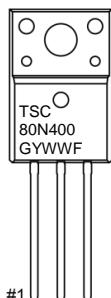
**Source-Drain Diode Forward Current vs. Voltage**



**Normalized Thermal Transient Impedance, Junction-to-Case**



**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

**ITO-220S**

**MARKING DIAGRAM**


- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

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